

Product Summary

Symbol	Value	Unit
$I_{T(RMS)}$	25	A
$V_{DRM} V_{RRM}$	800	V
V_{TM}	1.55	V

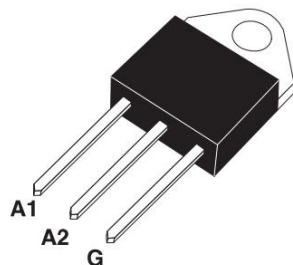
Feature

With high ability to withstand the shock loading of large current, With high commutation performances, 3 quadrants products especially recommended for use on inductive load.

Application

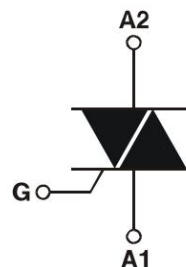
Washing machine, vacuums, massager, solid state relay, AC Motor speed regulation and so on.

Package

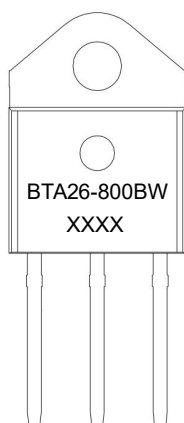


TO-3P Insulated

Circuit diagram



Marking



Absolute maximum ratings (Ta=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Repetitive peak off-state voltage	V_{DRM}	800	V
Repetitive peak reverse voltage	V_{RRM}	800	V
RMS on-state current	$I_{T(RMS)}$	25	A
Non repetitive surge peak on-state current (full cycle, F=50Hz)	I_{TSM}	250	A
I^2t value for fusing (tp=10ms)	I^2t	340	A
Critical rate of rise of on-state current ($I_G = 2 \times I_{GT}$)	di/dt	50	A/ μ s
Peak gate current	I_{GM}	4	A
Average gate power dissipation	$P_{G(AV)}$	1	W
Junction Temperature	T_J	-40 ~ +125	°C
Storage Temperature	T_{STG}	-40 ~ +150	°C

Electrical characteristics (Ta=25 °C, unless otherwise noted)

Parameter	Symbol	Test Condition		Value		Unit
Gate trigger current	I _{GT}	V _D =12V R _L = 33Ω	I - II -III	MAX.	50	mA
Gate trigger voltage	V _{GT}		I - II -III	MAX.	1.3	V
Gate non-trigger voltage	V _{GD}	V _D =V _{DRM} T _j =125 °C R _L =3.3KΩ	I - II -III	MIN.	0.2	V
latching current	I _L	I _G =1.2I _{GT}	I - II -III	MAX.	100	mA
Holding current	I _H	I _T =100mA		MAX.	50	mA
Critical-rate of rise of commutation voltage	dV/dt	V _D =2/3V _{DRM} Gate Open T _j =125°C		MIN.	1000	V/μs
STATIC CHARACTERISTICS						
Forward "on" voltage	V _{TM}	I _{TM} =35A tp=380μs		MAX.	1.55	V
Repetitive Peak Off-State Current	I _{DRM}	V _D =V _{DRM} V _R =V _{RRM}	T _j =25°C	MAX.	10	μA
Repetitive Peak Reverse Current	I _{RRM}		T _j =125°C	MAX.	3	mA
THERMAL RESISTANCES						
Thermal resistance	Rth(j-c)	Junction to case(AC)		TYP.	0.9	°C/W
	Rth(j-a)	Junction to ambient		TYP.	50	°C/W

Typical Characteristics

FIG1 Maximum power dissipation versus RMS on-state current

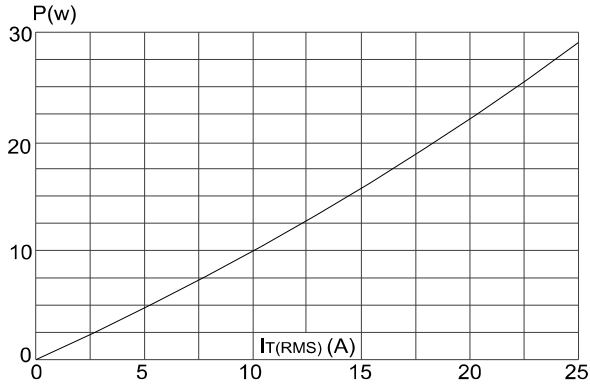


FIG2 RMS on-state current versus case temperature

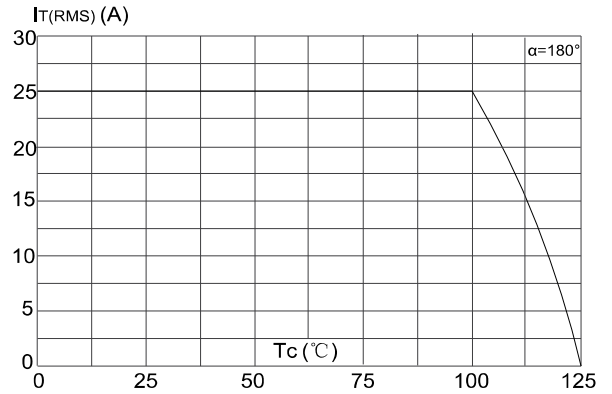


FIG3 Surge peak on-state current versus number of cycles

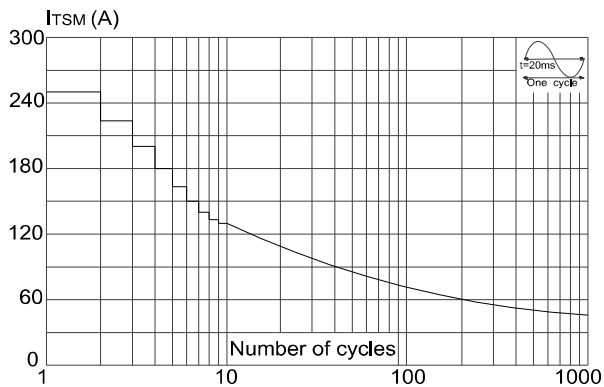


FIG4 On-state characteristics (maximum values)

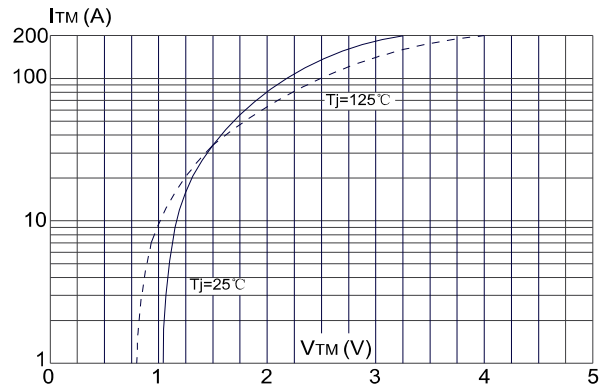


FIG5 Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 20ms$, and corresponding value of $I^2 t$ ($dI/dt < 100A/\mu s$)

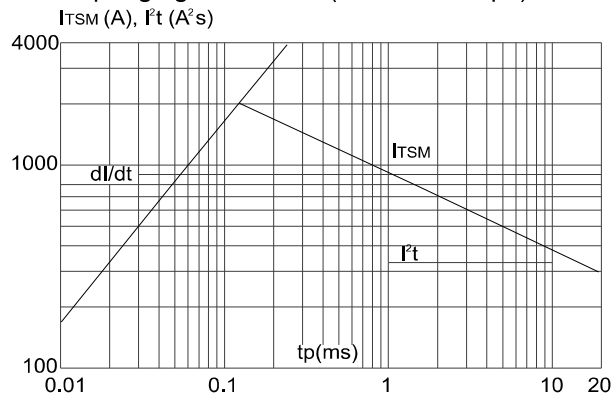
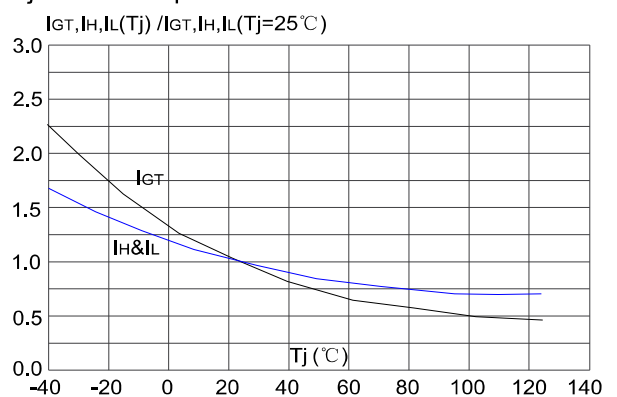
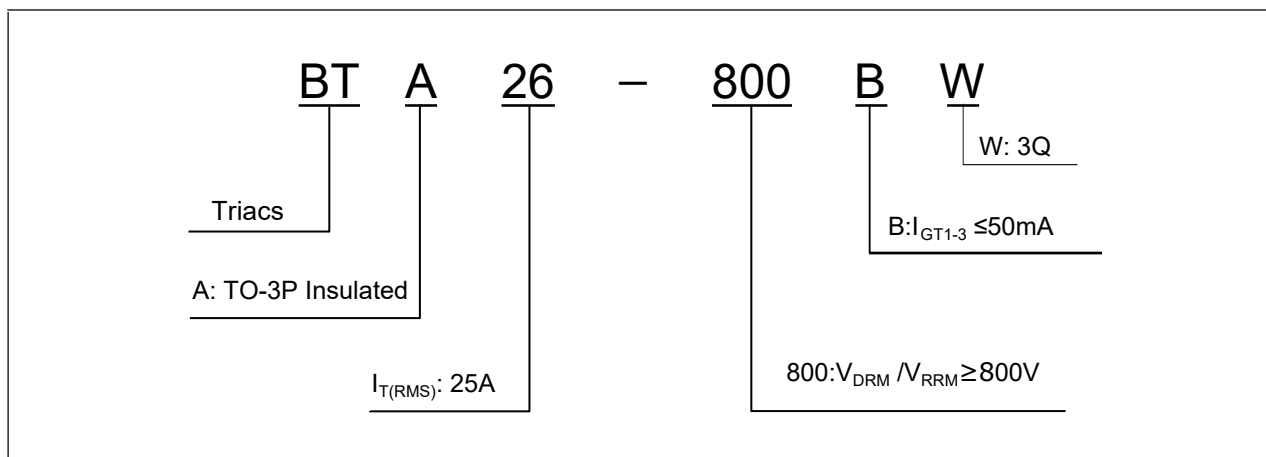


FIG6 Relative variations of gate trigger current, holding current and latching current versus junction temperature



Ordering Information



TO-3P Insulated Package Information

